

**PROCESS FOR PREPARING A STABILIZED  
IDEAL OXYGEN PRECIPITATING SILICON WAFER**

**ABSTRACT**

The present invention is directed to a single crystal Czochralski-type silicon wafer, and a process for the preparation thereof, which has a non-uniform distribution of stabilized oxygen precipitate nucleation centers therein.

Specifically, the peak concentration is located in the wafer bulk and a  
5 precipitate-free zone extends inward from a surface.